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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**



Application Number **10/038,745**
 Filing Date **January 2, 2002**
 First Named Inventor **Robert Jackson**
 Group Art Unit **1754**
 Examiner Name **Ngoc Nguyen**
 Attorney Docket Number **FOC1100-1**

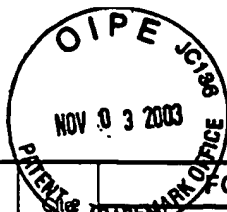
OF 1

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Examiner Initials	Cite No.	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear
		Number	Kind Code (if known)			
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Ngoc - yen Nguyen

6/17/06



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Examiner Signature	Ngaz-yen Nguyen				Date Considered	6/17/06	

FORM PTO 1449 US Department of Commerce Patent and Trademark Office NOV 03 2003		Application Number	10/038,745
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		Examiner Name	Ngoc Nguyen
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	C3	Astron, "Reactive Gas Generators," MKS Instruments, Inc., 4 pages.	
	C4	Chen, et al, "Advances in Remote Plasma Sources for Cleaning 300 mm and Flat Panel CVD Systems, Semiconductor Magazine."	August 2003
	C5	Kranefuss, "Etching System," IBM Technical Disclosure Bulletin, Vol. 9, No. 8, pg. 2956.	January 1977
	C6	"Anisotropic and Selective Etching of Tungsten Silicide-Tungsten-Tungsten Silicide Composite Stack," IBM Technical Disclosure Bulletin, Vol. 29, No. 3., pg. 1151.	August 1986
	C7	Bergendahl, et al., "Positive Photoresist for Permeation Etching," IBM Technical Disclosure Bulletin, Vol. 23, No. 10, pg. 4446.	March 1981
	C8	Flamm et al., "Reaction of Fluorine Atoms with SiO ₂ ," J. Appl. Phys., 50 (10), pages 6211-3,	October 1980
	C9	Donnelly et al., "Studies of Chemiluminescence Accompanying Fluorine Atom Etching of Silicon," J. Appl. Phys., 51 (10), pages 5273-6.	October 1980
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	C11	Mucha et al., "Chemiluminescence and the Reaction of Molecular Fluorine with Silicon," J. Phys. Chem., Vol. 85, Pages 3529-3532.	1981
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Ngoc - Yen Nguyen

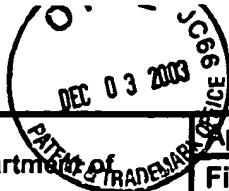
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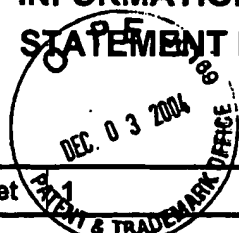
PTO/SB/08A (04-03)

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Examiner Signature		Ngoc - yun Nguyen			Date Considered	6/17/06	



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yn	C15	Working Agreement between Syngen Enterprises Ltd. and Fluorogas Ltd., Client I: Applied Materials, Exhibit P-1.			October 1998
yn	C16	Working Agreement between Syngen Enterprises Ltd. and Fluorogas Ltd., Client II: Novellus, Exhibit P-2.			October 1998
Examiner Signature	Ngoc Nguyen			Date Considered	6/17/06

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Sheet 1 OF 1

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 Examiner
Signature

/Ngoc Yen Nguyen/ (06/17/2006)

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